

APPENDIX

Claims 1 and 7 now read as follows:

1. (Amended) A semiconductor device comprising:

a semiconductor chip,

a protective insulating layer covering the surface of the semiconductor chip;

a plurality of connecting conductors connected to the surface of the semiconductor chip and penetrating the protective insulating layer beyond the outside surface of the protective insulating layer;

wherein the connecting conductor includes a plurality of layers formed of same material and at least one of the layers is formed as a stress-absorbing layer having lower hardness than other layer.

7. (Amended) A semiconductor device comprising:

a semiconductor chip,

a protective insulating layer covering the surface of the semiconductor chip;

a plurality of connecting conductors connected to the surface of the semiconductor chip and penetrating the protective insulating layer beyond the outside surface of the protective insulating layer;

wherein the connecting conductor includes a plurality of layers formed of different material and at least one of the layers is formed as a stress-absorbing layer having lower hardness than other layer.